

Applications

- SMPS Synchronous Rectification
- DC/DC Converters
- ORING

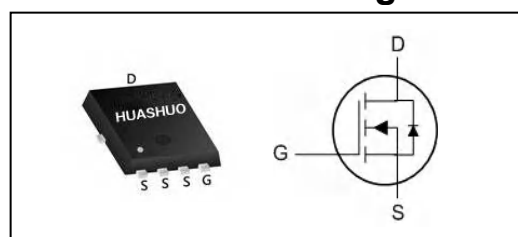
Features

- Advanced SGT MOS MOS Technology
- Low $R_{DS(on)}$
- 100% EAS Guaranteed
- Green Device Available

Product Summary

V_{DS}	40	V
$R_{DS(ON),TYP}$	1.6	m Ω
I_D	130	A

PRPAK3X3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current ^{1,6}	130	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current ^{1,6}	81	A
I_{DM}	Pulsed Drain Current ²	520	A
EAS	Single Pulse Avalanche Energy ³	362	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	60	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	65	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.1	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	1.6	2.2	mΩ
		V _{GS} =4.5V, I _D =20A	---	2.2	2.9	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.7	2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =32V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =32V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.8	---	Ω
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _D =20A	---	35	---	nC
Q _{gs}	Gate-Source Charge		---	6	---	
Q _{gd}	Gate-Drain Charge		---	8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =20V, V _{GS} =10V, R _G =1Ω I _D =1A	---	8	---	ns
T _r	Rise Time		---	9.6	---	
T _{d(off)}	Turn-Off Delay Time		---	32	---	
T _f	Fall Time		---	15	---	
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1MHz	---	2290	---	pF
C _{oss}	Output Capacitance		---	913	---	
C _{rss}	Reverse Transfer Capacitance		---	88	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	130	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _f =20A, dI/dt=100A/us	---	41	---	ns
Q _{rr}	Reverse Recovery Charge	I _f =20A, dI/dt=100A/us	---	26	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.5mH, R_G=25Ω
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

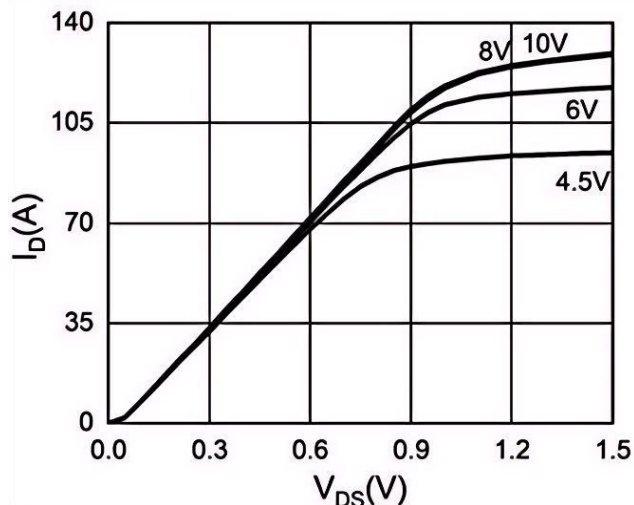


Fig.1 Typical Output Characteristics

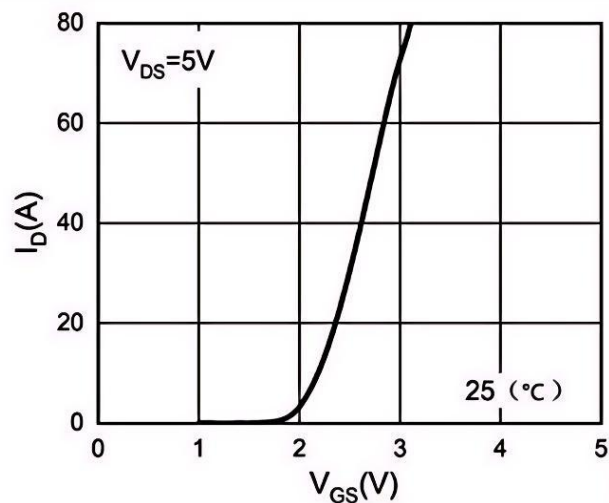


Fig.2 Transfer Characteristics

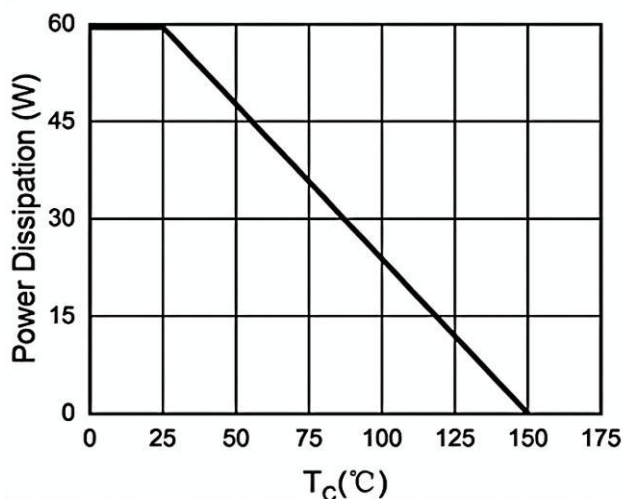


Fig.3 Power Dissipation

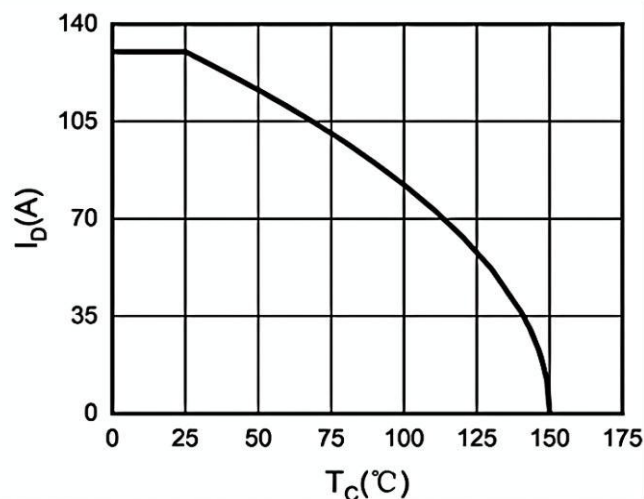


Fig.4 Drain Current

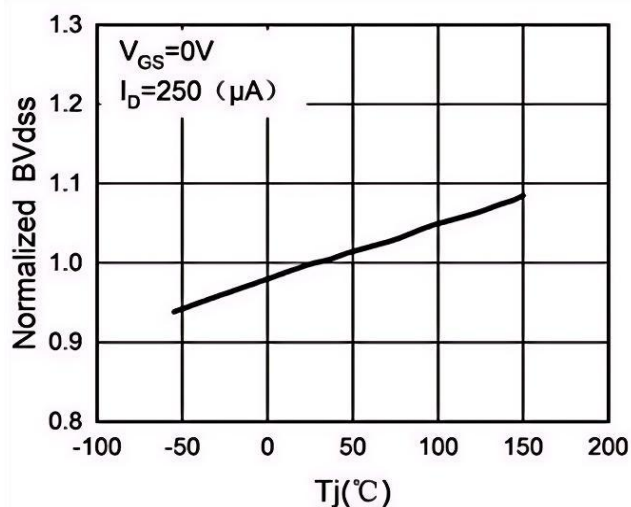


Fig.5 BV_{DS} vs Junction Temperature

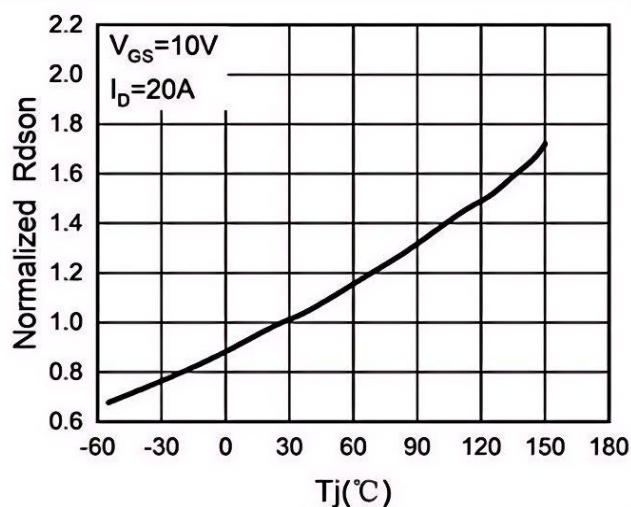


Fig.6 R_{DS(ON)} vs Junction Temperature

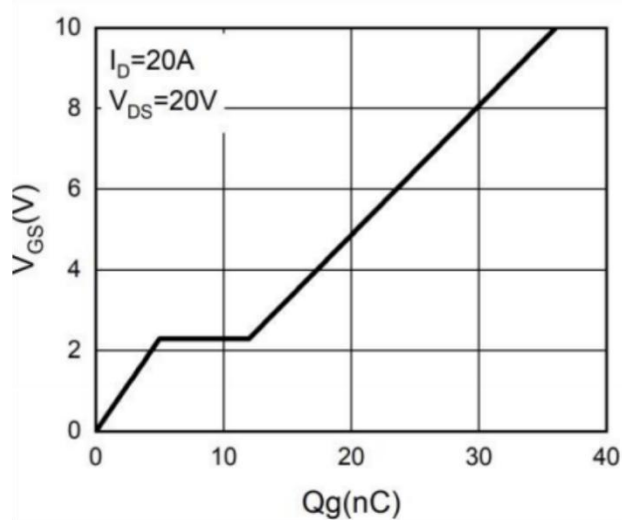


Fig.7 Gate Charge Waveforms

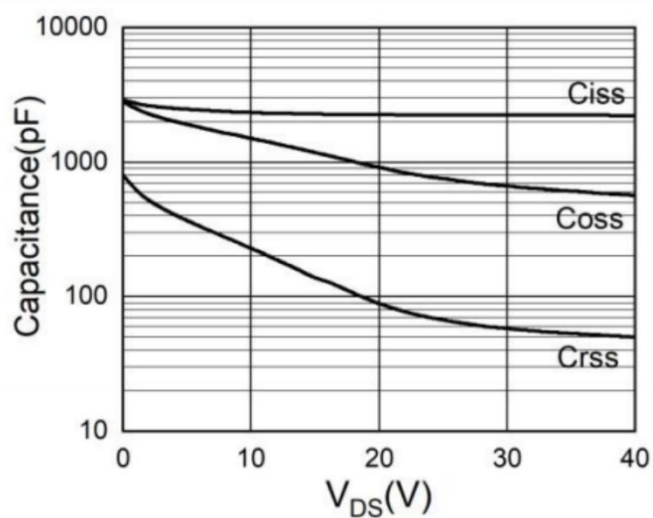


Fig.8 Capacitance

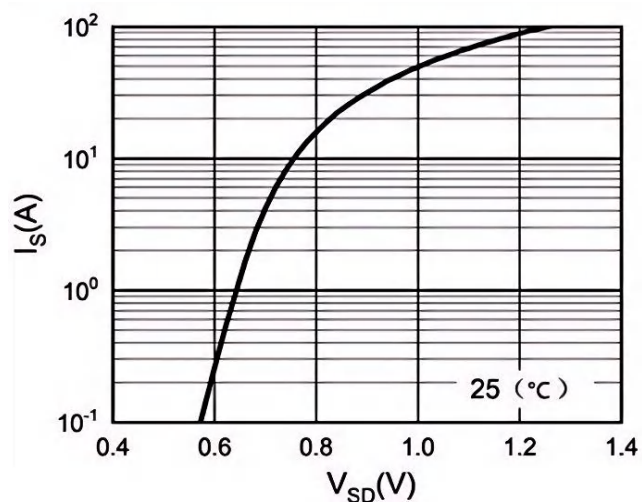


Fig.9 Body Diode Characteristics

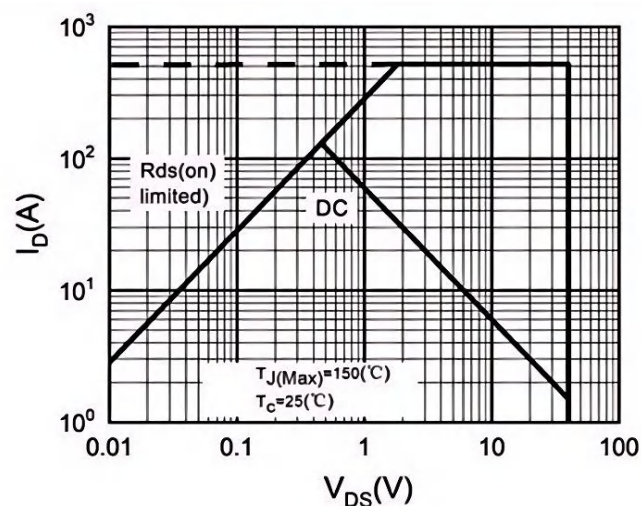
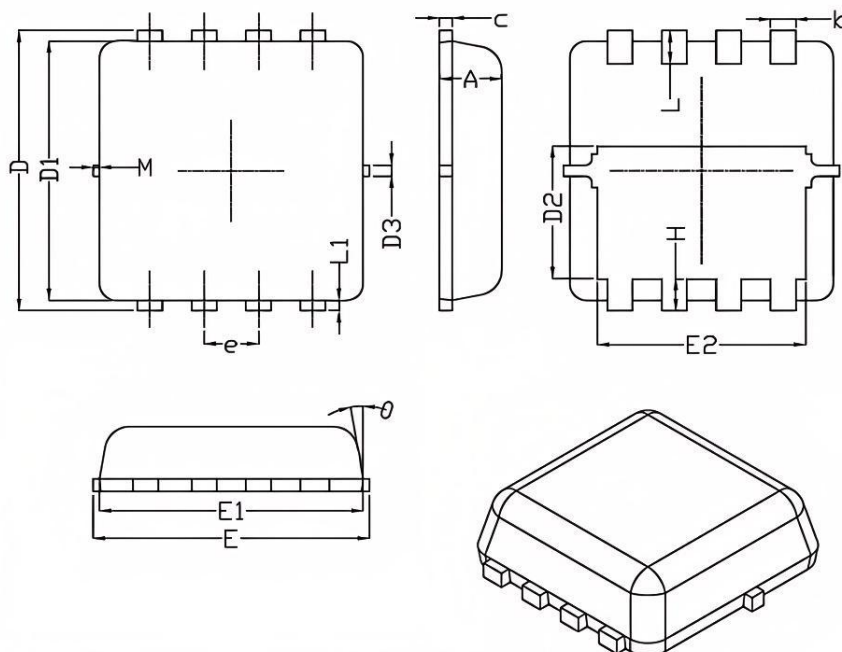


Fig.10 Maximum Safe Operating Area

Ordering Information

Part Number	Package code	Packaging
HSBB4076	PRPAK3*3	3000/Tape&Reel

PRPAK3*3(E) Single Package Outline



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
C	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.15	3.30	3.45
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

HSBB4076 Marking:

